Silicon PNP Power Transistors 2SA1133 2SA1133A

DESCRIPTION

·With TO-220 package
·High breakdown voltage
·High power dissipation
·Complement to type 2SC2660/2660A

APPLICATIONS

·For power amplifier and TV vertical deflection output applications

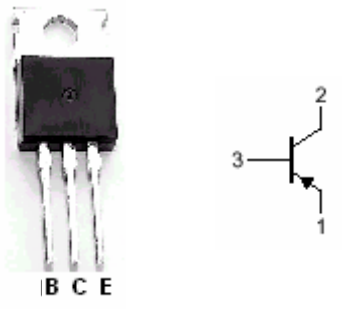

Fig.1 simplified outline (TO-220) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	2SA1133	Open base	-150	V
		2SA1133A		-180	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-2.0	A
I_{CM}	Collector current-peak			-3.0	A
P_T	Total power dissipation		T_C=25□	30	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA1133	I_C=-5mA ,I_B=0	-150			V
		2SA1133A		-180			
$V_{(BR)CBO}$	Collector-base breakdown voltage		I_C=-0.5mA ,I_E=0	-200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=-0.5mA ,I_C=0	-6			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=-500mA; I_B=-50mA			-1.0	V
V_{BE}	Base-emitter on voltage		I_C=-400mA ; V_{CE}=-10V			-1.0	V
I_{CBO}	Collector cut-off current		V_{CB}=-200V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current		V_{EB}=-4V; I_C=0			-50	μA
h_{FE-1}	DC current gain		I_C=-150m A ; V_{CE}=-10V	60		240	
h_{FE-2}	DC current gain		I_C=-400mA ; V_{CE}=-10V	50			

◆ **h_{FE-1} Classifications**

Q	P
60-140	100-240

PACKAGE OUTLINE

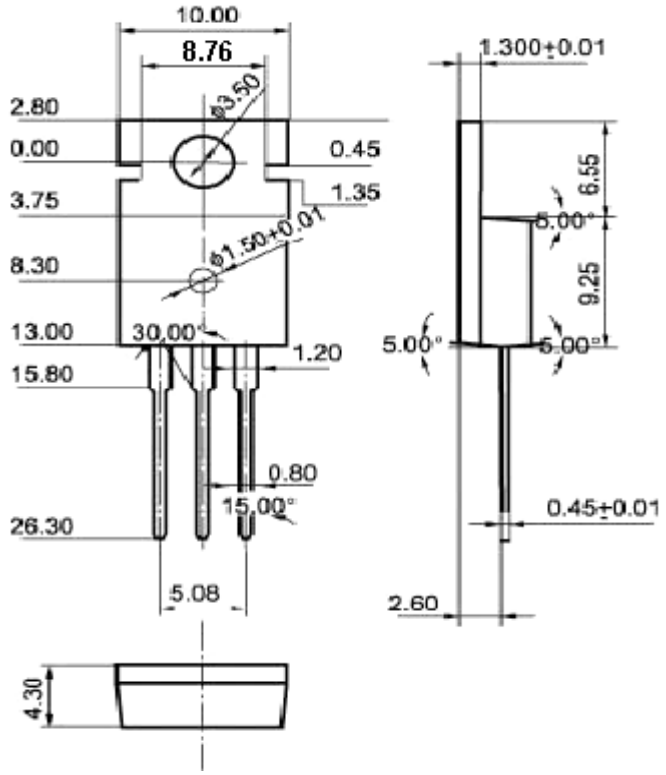

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)